

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33$	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM} T_j=125 R_L=3.3K$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	60	mA
I_H	$I_T=500mA$	-	-	50	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$	500	-	-	V s
t_{on}	$I_G=20mA I_A=200mA I_R=20mA$ $T_j=25$	-	5	-	s
t_{off}		-	80	-	

Symbol**Parameter****Value(MAX.)**

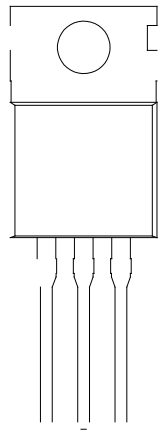
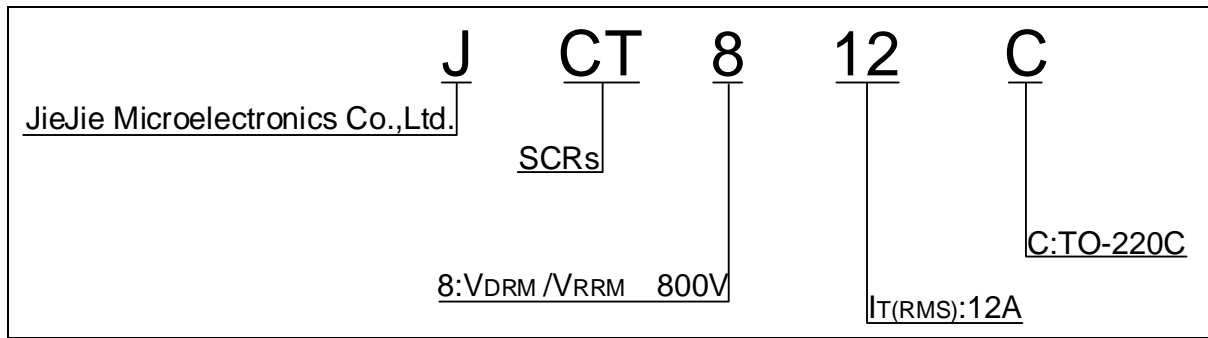


FIG.1 Maximum power dissipation versus RMS on-state current

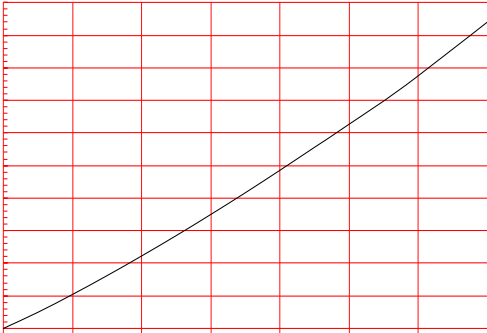


FIG.2: RMS on-state current versus case temperature

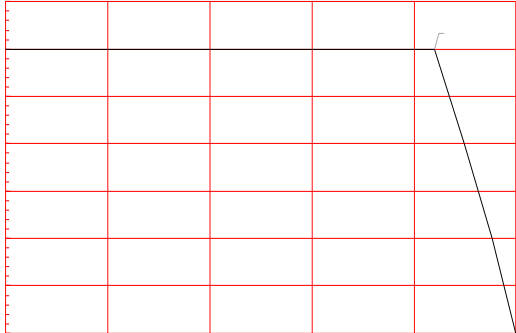
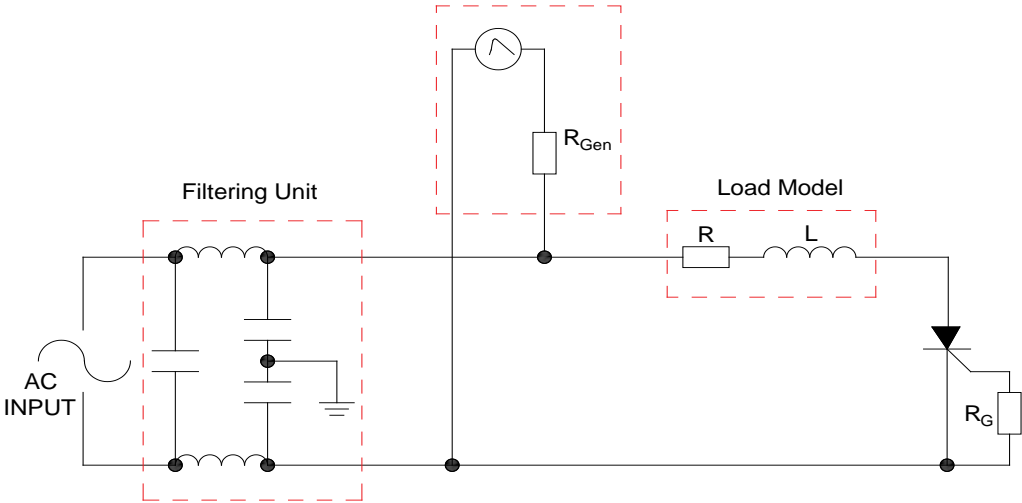


FIG.3: Surge peak on-state current versus number of cycles

FIG.4: On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.

IEC61000-4-5 Standards
Surge Generator




Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT812C	800	15	TO-220C	50	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update

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